

ABSTRACT OF THE DISCLOSURE

In an active matrix drive light emitting device, above a thin film transistor, a light emitting element having an anode, a layer comprised of an organic compound and a cathode containing an alkali metal is formed between a third insulating layer comprised of silicon nitride or silicon oxynitride and a fourth insulating layer containing carbon as its main constituent. The light emitting element is formed between partition layers that are formed of an insulating material and have an inverse tapered shape.